

**PCN 15\_0156 ADG836 Wafer Fabrication Change from TSMC Fab 7A to TSMC Fab 11**

<b>QUALIFICATION RESULTS</b>			
<b>TEST</b>	<b>SPECIFICATION</b>	<b>SAMPLE SIZE</b>	<b>RESULTS</b>
High Temperature Operating Life (HTOL)*	JEDEC <i>JESD22-A108</i>	<b>2x45</b> <b>7x77</b>	<b>Pass</b>
Highly Accelerated Stress Test (HAST)*	JEDEC <i>JESD22-A110</i>	<b>4x77</b> <b>5x45</b>	<b>Pass</b>
ELF	MIL-STD-883, <i>Method 1015</i>	<b>3x667</b> <b>3x667</b> <b>3x667</b>	<b>Pass</b>
High Temperature Storage Life (HTSL)	JEDEC <i>JESD22-A103</i>	<b>1x77</b> <b>3x45</b>	<b>Pass</b>
Latch-Up	JEDEC <i>JESD78</i>	<b>3</b>	<b>Pass</b>
Electrostatic Discharge <i>Human Body Model</i>	ESDA/JEDEC <i>JS-001</i>	<b>3/voltage</b>	<b>Pass_4000V</b>
Electrostatic Discharge <i>Machine Model</i>	JEDEC <i>JESD22-A115</i>	<b>3/voltage</b>	<b>Pass_200V</b>
Electrostatic Discharge <i>Field-Induced Charged Device Model</i>	JEDEC <i>JESD22-C101</i>	<b>3/voltage</b>	<b>Pass_1250V</b>

\*Preconditioned per JEDEC/IPC J-STD-020